

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2461	@ad<="20031229" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:30
L2	308	@ad<="20031229" and (257/69).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:31
L3	183	@ad<="20031229" and (257/195).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:31
L4	668	@ad<="20031229" and (257/300).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:31
L5	476	@ad<="20031229" and (257/204).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:31
L6	1687	@ad<="20031229" and (438/591-592).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:32
L7	576	@ad<="20031229" and (438/587-588).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:32
L8	1165	@ad<="20031229" and (438/585).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:33
L9	752	@ad<="20031229" and (438/199).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:33
L10	880	@ad<="20031229" and (438/227-228).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:33
S1	19	@ad<="20031229" and 'CMOS' and 'metal gate' same 'NMOS' and 'silicide gate' same 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:03

S2	1	"6506642".PN.	USPAT; USOCR	OR	ON	2005/02/25 13:30
S3	1	"6166417".PN.	USPAT; USOCR	OR	ON	2005/02/25 13:33
S4	1	"5949092".PN.	USPAT; USOCR	OR	ON	2005/02/25 13:38
S5	190	@ad<="20031229" and 'CMOS' and 'metal' with 'NMOS' and 'silicide' with 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 13:56
S6	75	@ad<="20031229" and 'CMOS' and 'metal gate' and 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:25
S7	31	@ad<="20031229" and 'CMOS' and 'metal gate' same 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 13:57
S8	1	"6586321".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:00
S9	1	"6506642".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:01
S10	1	"6475908".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:01
S11	1	"6589836".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:05
S12	1	"6294434".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:06
S13	1	"6177335".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:07
S14	1	"5122479".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:07
S15	1	"5236872".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:07
S16	14	@ad<="20031229" and 'NMOS' with 'metal gate' and 'PMOS' with 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 14:36
S17	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:31
S18	1	"6274511".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:33
S19	1	"6083836".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:33
S20	1	"6051487".PN.	USPAT; USOCR	OR	ON	2005/02/25 14:34

S21	62	@ad<="20031229" and 'dual gate' with 'metal' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 14:37
S22	216	@ad<="20031229" and 'CMOS' and 'metal' same 'NMOS' and 'metal silicide' same 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 15:09
S23	85	@ad<="20031229" and 'CMOS' and 'metal' with 'NMOS' and 'metal silicide' with 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 06:24
S24	1	"6586321".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:10
S25	1	"20020008294".PN.	US-PGPUB	OR	ON	2005/02/25 15:19
S26	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:20
S27	1	"6204103".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:20
S28	1	"6204103".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:20
S29	1	"5656519".PN.	USPAT; USOCR	OR	ON	2005/02/25 15:20
S31	0	@ad<="20031229" and 'polysilicon' same 'remove' and 'p-type polysicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/25 16:03
S32	3	@ad<="20031229" and 'polysilicon' same 'remove' and 'p-type polysilicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:22
S33	19	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 08:51
S34	1	"20020058374".PN.	US-PGPUB	OR	ON	2005/02/25 16:07
S35	1	"6586288".PN.	USPAT; USOCR	OR	ON	2005/02/25 16:07
S36	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/02/25 16:07
S37	1	"6365450".PN.	USPAT; USOCR	OR	ON	2005/02/25 16:07
S38	1	"6255698".PN.	USPAT; USOCR	OR	ON	2005/02/25 16:10

S39	1681	@ad<="20031229" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:31
S40	812	@ad<="20031229" and (257/310).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:04
S41	1589	@ad<="20031229" and (438/591-592).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:32
S42	956	@ad<="20031229" and (438/585).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:33
S43	554	@ad<="20031229" and (438/587-588).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:32
S44	680	@ad<="20031229" and (438/199).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:33
S45	508	@ad<="20031229" and (438/227-228).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:33
S46	1	@ad<="20031229" and 'NMOS' and 'PMOS' and 'p-type polysilicon' and 'remove' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:26
S47	4	@ad<="20031229" and 'remove' and 'p-type polysilicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:22
S48	2	"20040099916"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 08:27
S49	368	@ad<="20031229" and 'CMOS' and 'n-type' with 'metal' and 'p-type' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:29

S50	2	@ad<="20031229" and 'CMOS' and 'n-type metal' and 'p-type silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:29
S51	22	@ad<="20031229" and 'CMOS' and 'n-type' with 'metal' and 'p-type' with 'cobalt silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:32
S52	4	@ad<="20031229" and 'CMOS' and 'n-type' with 'metal' same 'p-type' with 'cobalt silicide' same 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:30
S53	4	@ad<="20031229" and 'CMOS' and 'n-type' with 'metal' same 'p-type' with 'cobalt silicide' same 'electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 09:30
S54	48	@ad<="20031229" and 'hafnium oxide' same 'atomic' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:34
S55	10	@ad<="20031229" and 'hafnium oxide' with 'atomic' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:52
S56	0	brask-justin.in. and 'intel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:52
S57	0	brask-justin.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 10:53
S58	12	'brask justin' and 'Intel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/28 11:01
S59	12	'brask' adj1 'justin' and 'Intel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:07
S60	19	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:17

S61	53	@ad<="20031229" and 'CMOS' and 'polysilicon' with 'silicide' and 'n-type metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:13
S62	1	"20020058374".PN.	US-PGPUB	OR	ON	2005/04/19 08:52
S63	1	"6586288".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:05
S64	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:05
S65	1	"6365450".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:06
S66	1	"6255698".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:07
S68	533	@ad<="20031229" and 'CMOS' same 'silicide' with 'metal' with 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:14
S69	82	@ad<="20031229" and 'CMOS' and 'metal gate' and 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:42
S70	864	@ad<="20031229" and 'CMOS' same 'dual gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 09:43
S71	103	@ad<="20031229" and 'CMOS' same 'dual gate' and 'work function'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 07:39
S72	1	"6200866".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:53
S73	1	"6033963".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:53
S74	1	"5966597".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:53
S75	1	"5960270".PN.	USPAT; USOCR	OR	ON	2005/04/19 09:53
S76	16	'brask' adj1 'justin' and 'Intel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:09
S77	29	chau-robert.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:12

S78	12	thomas-christopher.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:13
S79	13	datta-suman.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:13
S80	419	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' and 'n-type polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:38
S81	22	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' and 'n-type polysilicon' and 'selective etching'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 10:47
S82	31	@ad<="20031229" and 'p-type polysilicon' and 'n-type polysilicon' and 'selective etch'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:05
S83	0	cha-liang-cher.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:06
S84	0	cher-liang-cha.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:06
S85	0	cha-liang.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:06
S86	3	'cher liang cha' and 'chartered semiconductor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:31
S87	59	@ad<="20031229" and 'CMOS' and 'p-type polysilicon' with 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:17
S88	315	@ad<="20031229" and 'CMOS' and 'chartered semiconductor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 11:31

S89	2	("6645818").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/29 14:00
S90	1	"6514827".PN.	USPAT; USOCR	OR	ON	2005/07/29 13:57
S91	1	"6303418".PN.	USPAT; USOCR	OR	ON	2005/07/29 13:59
S92	1	"6184083".PN.	USPAT; USOCR	OR	ON	2005/07/29 13:59
S93	5	"2004018681"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:01
S94	7	'pham' with 'thanh' with 'khac'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:10
S95	31	'mona' with 'eissa'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:10
S96	31	'mona' with 'eissa' and 'texas'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:23
S97	1	"6624086".PN.	USPAT; USOCR	OR	ON	2005/07/29 14:12
S98	1	"6555879".PN.	USPAT; USOCR	OR	ON	2005/07/29 14:12
S99	1	"6551943".PN.	USPAT; USOCR	OR	ON	2005/07/29 14:12
S100	1	"6514808".PN.	USPAT; USOCR	OR	ON	2005/07/29 14:12
S101	1	"6455330".PN.	USPAT; USOCR	OR	ON	2005/07/29 14:12
S102	1	"6284721".PN.	USPAT; USOCR	OR	ON	2005/07/29 14:12
S103	0	'wo 0471663'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:23
S104	0	'WO 0471663'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:23

S10 5	0	'WO 04/71663'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:23
S10 6	0	'WO 471663'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:26
S10 7	0	'200567034'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:26
S10 8	0	'WO 0567034'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:28
S10 9	0	'WO 05/67034'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:29
S11 0	0	'WO S93 67034'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:27
S11 1	0	'200567034'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:28
S11 4	1	"20050148136"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:42
S11 6	39	'takeuchi' with 'kiyoshi' and 'nec'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/29 14:42
S11 7	1	"6514827".PN.	USPAT; USOCR	OR	ON	2005/07/30 05:31
S11 8	1	"6410376".PN.	USPAT; USOCR	OR	ON	2005/07/30 05:55
S11 9	1	"6274511".PN.	USPAT; USOCR	OR	ON	2005/07/30 06:00
S12 0	1	"6083836".PN.	USPAT; USOCR	OR	ON	2005/07/30 06:00
S12 1	1	"6051487".PN.	USPAT; USOCR	OR	ON	2005/07/30 06:01

S12 2	1	"6043157".PN.	USPAT; USOCR	OR	ON	2005/07/30 06:01
S12 3	231	'CMOS' and 'metal' with 'NMOS' and 'silicide' with 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 06:04
S12 4	91	'CMOS' and 'metal' with 'NMOS' and 'polysilicon' same 'silicide' with 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 06:04
S12 5	93	@ad<="20031229" and 'CMOS' and 'metal' with 'NMOS' and 'metal silicide' with 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 07:00
S12 6	15	@ad<="20031229" and 'CMOS' and 'metal gate' with 'NMOS' and 'silicide gate' with 'PMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 07:01
S12 7	15	@ad<="20031229" and 'NMOS' with 'metal gate' and 'PMOS' with 'silicide gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 07:24
S12 8	2	("6303418").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/30 07:24
S12 9	1	"6200866".PN.	USPAT; USOCR	OR	ON	2005/07/30 07:25
S13 0	1	"6033963".PN.	USPAT; USOCR	OR	ON	2005/07/30 07:25
S13 1	1	"5966597".PN.	USPAT; USOCR	OR	ON	2005/07/30 07:26
S13 2	1	"5960270".PN.	USPAT; USOCR	OR	ON	2005/07/30 07:26
S13 3	1	"5731239".PN.	USPAT; USOCR	OR	ON	2005/07/30 07:26
S13 4	33	@ad<="20031229" and 'CMOS' same 'dual gate' same 'work function'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 07:41
S13 6	67	@ad<="20031229" and 'CMOS' same 'dual gate' and 'work function' and 'silicide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 07:43

S13 7	108	@ad<="20031229" and 'CMOS' same 'dual gate' and 'work function'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 07:47
S13 8	108	@ad<="20031229" and 'CMOS' same 'dual gate' and 'work function'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/30 07:47